This GIDEP PCN is to announce a change in the electrical characteristics for the following International Rectifier Part No listed below.

**IRHY67C30CM (2N7599T3)**
600V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a TO-257AA package

**Electrical Characteristics @ Tj = 25°C**

- **RDS(on)** Static Drain-to-Source On-State Resistance
  @ VGS = 12V, ID = 2.1A,  Change from 3.0Ω to 3.1Ω

- **Qg** Total Gate Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  Change from 35nC to 52nC

- **Qgs** Gate-to-Source Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  Change from 12nC to 14nC

- **Qgd** Gate-to-Drain (‘Miller’) Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  Change from 15nC to 17nC

- **td(on)** Turn-On Delay Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  Change from 18nS to 25nS

- **tr** Rise Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  Change from 12nS to 17nS

- **td(off)** Turn-Off Delay Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  Change from 36nS to 44nS

- **tf** Fall Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  Change from 14nS to 17nS

Reference: IR Datasheet PD-95837